

Develop low-loss, compact SiC modules

SiC modules

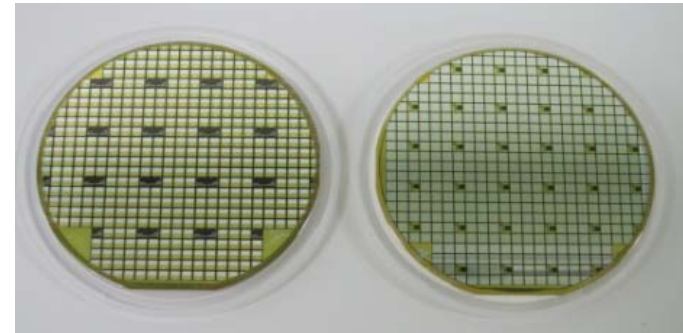
- High-speed switching low-loss full SiC modules using SiC-SBD and MOS devices
- New-type high-temperature (200°C) compatible packages with 75% less volume than previously developed products



SiC power devices

MOSFET

SBD



* Through joint development with National Institute of Advanced Industrial Science and Technology (incorporated administrative agency)

Device structure

